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(71) Applicant (for all designated States except US): SEMICONDUCTOR CORPORA-FAIRCHILD TION [US/US]; 82 Running Hill Road, South Portland, ME 04106 (US).

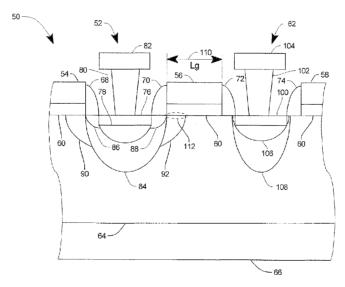
- (72) Inventor; and
- (75) Inventor/Applicant (for US only): CAI, Jun [CN/US]; 20 Longmeadow Road, Scarborough, ME 04074 (US).
- (74) Agent: FITZGERALD, Thomas, R.; Hiscock & Barclay, LLP, 2000 HSBC Plaza, Rochester, NY 14604-2404 (US).

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(57) Abstract: The invention includes a laterally double-diffused metal-oxide semiconductor (LDMOS) having a reduced size, a high breakdown voltage, and a low on-state resistance. This is achieved by providing a thick gate oxide on the drain side of the device, which reduces electric field crowding in the off-state to reduce the breakdown voltage and forms an accumulation layer in the drift region to reduce the device resistance in the on-slate. A version of the device includes a low threshold voltage version with a thin gate oxide on the source side of the device and a high threshold voltage version of the device includes a thick gate oxide on the source side. The LDMOS may be configured in an LNDMOS having an N type source or an LPDMOS having a P type source. The source of the device is fully aligned under the oxide spacer adjacent the gate to provide a large SOA, to reduce the device size and to reduce the device leakage.





### INTERNATIONAL SEARCH REPORT

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A. CLASSIFICATION OF SUBJECT MATTER IPC(8) - H01L 29/76 (2007.10) USPC - 257/343			
According to International Patent Classification (IPC) or to both national classification and IPC			
B. FIELDS SEARCHED			
Minimum documentation searched (classification system followed by classification symbols) USPC: 257/343			
Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched 438/527; 438/268; 257/341; (text search, see terms below)			
Electronic data base consulted during the international search (name of data base and, where practicable, search terms used) PubWEST(PGPB,USPT,EPAB,JPAB); Google, Google Scholar Search Terms: LDMOS, MOS, lateral, well, trench, oxide			
C. DOCUMENTS CONSIDERED TO BE RELEVANT			
Category*	Citation of document, with indication, where app	propriate, of the relevant passages	Relevant to claim No.
X - Y	US 6,413,822 B2 (WILLIAMS et al.) 02 July 2002 (02.07 11, in 51-61, col 19, in 4 to col 20, in 34, in 1 to col 23, i	7.2002), col 1, ln 7-24, col 2, ln 1-8, col n 33, Fig 23	1-31, 33, 34  32
Υ	US 6,844,585 B1 (HOPPER et al.) 18 January 2005 (18	3.01.2005), col 2, ln 35-56	32
Α	US 2005/0073003 A1 (TORNBLAD et al.) 07 April 2005 (07.04.2005), entire document		1-34
Α	US 2003/0178673 A1 (BHALLA et al.) 25 September 2003 (25.09.2003), entire document		1-34
Α	US 2003/0080379 A1 (OIKAWA et al.) 01 May 2003 (01.05.2003), entire document		1-34
Α	US 5,557,127 A (AJIT et al.) 17 September 1996 (17.09.1996), entire document		1-34
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